

FEATURES

Fast slew rate: 22 V/ μ s typical
Settling time (0.01%): 1.2 μ s maximum
Offset voltage: 200 μ V typical
High open-loop gain: 1000 V/mV minimum
Low total harmonic distortion: 0.002% typical

APPLICATIONS

Output amplifier for fast DACs
 Signal processing
 Instrumentation amplifiers
 Fast sample-and-holds
 Active filters
 Low distortion audio amplifiers
 Input buffer for ADCs
 Servo controllers

GENERAL DESCRIPTION

The OP249 is a high speed, precision dual JFET op amp, similar to the popular single op amp. The OP249 outperforms available dual amplifiers by providing superior speed with excellent dc performance. Ultrahigh open-loop gain (1 kV/mV minimum), low offset voltage, and superb gain linearity makes the OP249 the industry's first true precision, dual high speed amplifier.

With a slew rate of 22 V/ μ s typical and a fast settling time of less than 1.2 μ s maximum to 0.01%, the OP249 is an ideal choice for high speed bipolar DAC and ADC applications. The excellent dc performance of the OP249 allows the full accuracy of high resolution CMOS DACs to be realized.

PIN CONFIGURATIONS

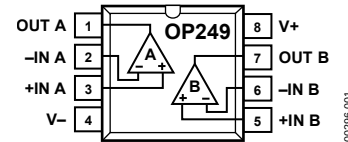


Figure 1. 8-Lead Cerdip (Q-8) and 8-Lead PDIP (N-8)

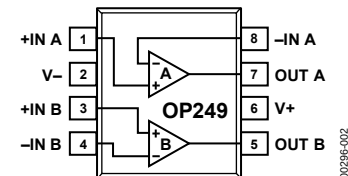


Figure 2. 8-Lead SOIC (R-8)

Symmetrical slew rate, even when driving large load, such as, 600 Ω or 200 pF of capacitance and ultralow distortion, make the OP249 ideal for professional audio applications, active filters, high speed integrators, servo systems, and buffer amplifiers.

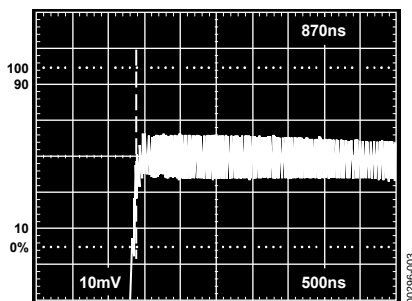


Figure 3. Fast Settling (0.01%)

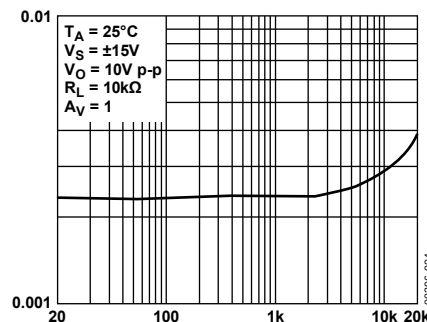


Figure 4. Low Distortion, $A_V = 1$, $R_L = 10\text{ k}\Omega$

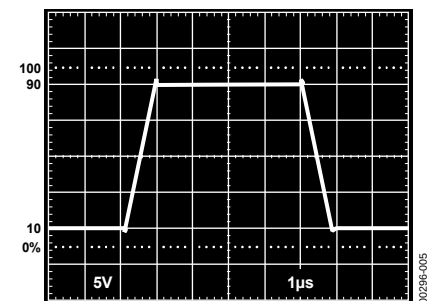


Figure 5. Excellent Output Drive, $R_L = 600\text{ }\Omega$

Rev. G

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REVISION HISTORY

4/10—Rev. F to Rev. G

Changes to Features Section and General Description Section ..	1
Changes to Offset Voltage Parameter, Table 1	3
Deleted Long Term Offset Voltage Parameter and Note 1, Table 1	3
Changes to Offset Voltage Parameter, Offset Voltage Temperature Coefficient Parameter, and Note 1, Table 3	5
Delete OP249F Columns, Table 3	5
Changes to Offset Voltage Parameter and Offset Voltage Temperature Coefficient Parameter, Table 4	5
Inserted OP249F Columns, Table 4	5
Changes to Discussion on Driving ADCs Section	16
Deleted Figure 52 and Figure 53	17

5/07—Rev. E to Rev. F

Updated Format	Universal
Changes to Table 1	3
Changes to Table 2	4
Changes to Table 3 and Table 4	5
Changes to Table 5	6
Changes to Figure 31	11
Changes to Figure 37 and Figure 38	12
Deleted OP249 SPICE Macro-Model Section	14
Deleted Figure 18; Renumbered Sequentially	14
Deleted Table I	15
Changes to Discussion on Driving ADCs Section	17
Updated Outline Dimensions	18
Changes to Ordering Guide	19

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9/01—Rev. D to Rev. E

Edits to Features and Pin Connections	1
Edits to Electrical Characteristics	2, 3
Edits to Absolute Maximum Ratings, Package Type, and Ordering Guide	4
Deleted Wafer Test Limits and Dice Characteristics Section	5
Edits to Typical Performance Characteristics	8
Edits to Macro-Model Figure	15
Edits to Outline Dimensions	17

SPECIFICATIONS

ELECTRICAL CHARACTERISTICS

$V_S = \pm 15\text{ V}$, $T_A = 25^\circ\text{C}$, unless otherwise noted.

Table 1.

Parameter	Symbol	Conditions	OP249A			OP249F			Unit
			Min	Typ	Max	Min	Typ	Max	
Offset Voltage	V_{OS}	$V_{CM} = 0\text{ V}$		0.2	0.75		0.2	0.9	mV
Offset Stability				1.5			1.5		$\mu\text{V/month}$
Input Bias Current	I_B	$V_{CM} = 0\text{ V}$, $T_A = 25^\circ\text{C}$		30	75		30	75	pA
Input Offset Current	I_{OS}	$V_{CM} = 0\text{ V}$, $T_A = 25^\circ\text{C}$		6	25		6	25	pA
Input Voltage Range ¹	I_{VR}			12.5			12.5		V
			± 11			± 11			V
				-12.5			-12.5		V
Common-Mode Rejection	CMR	$V_{CM} = \pm 11\text{ V}$	80	90		80	90		dB
Power-Supply Rejection Ratio	PSRR	$V_S = \pm 4.5\text{ V}$ to $\pm 18\text{ V}$		12	31.6		12	50	$\mu\text{V/V}$
Large Signal Voltage Gain	A_{VO}	$V_O = \pm 10\text{ V}$, $R_L = 2\text{ k}\Omega$	1000	1400		500	1200		V/mV
Output Voltage Swing	V_O	$R_L = 2\text{ k}\Omega$		12.5			12.5		V
			± 12.0			± 12.0			V
				-12.5			-12.5		V
Short-Circuit Current Limit	I_{SC}	Output shorted to ground		36			36		mA
			± 20		± 50	± 20		± 50	mA
				-33			-33		mA
Supply Current	I_{SY}	No load, $V_O = 0\text{ V}$		5.6	7.0		5.6	7.0	mA
Slew Rate	SR	$R_L = 2\text{ k}\Omega$, $C_L = 50\text{ pF}$	18	22		18	22		V/ μs
Gain Bandwidth Product ²	GBW		3.5	4.7		3.5	4.7		MHz
Settling Time	t_S	10 V step 0.01% ³		0.9	1.2		0.9	1.2	μs
Phase Margin	Θ_M	0 dB gain		55			55		Degrees
Differential Input Impedance	Z_{IN}			$10^{12} 6$			$10^{12} 6$		ΩpF
Open-Loop Output Resistance	R_O			35			35		Ω
Voltage Noise	e_n p-p	0.1 Hz to 10 Hz		2			2		$\mu\text{V p-p}$
Voltage Noise Density	e_n	$f_O = 10\text{ Hz}$		75			75		nV/ $\sqrt{\text{Hz}}$
		$f_O = 100\text{ Hz}$		26			26		nV/ $\sqrt{\text{Hz}}$
		$f_O = 1\text{ kHz}$		17			17		nV/ $\sqrt{\text{Hz}}$
		$f_O = 10\text{ kHz}$		16			16		nV/ $\sqrt{\text{Hz}}$
Current Noise Density	i_n	$f_O = 1\text{ kHz}$		0.003			0.003		pA/ $\sqrt{\text{Hz}}$
Voltage Supply Range	V_S		± 4.5	± 15	± 18	± 4.5	± 15	± 18	V

¹ Guaranteed by CMR test.

² Guaranteed by design.

³ Settling time is sample tested.

OP249

$V_S = \pm 15\text{ V}$, $T_A = 25^\circ\text{C}$, unless otherwise noted.

Table 2.

Parameter	Symbol	Conditions	OP249G			Unit
			Min	Typ	Max	
Offset Voltage	V_{OS}	$V_{CM} = 0\text{ V}$		0.4	2.0	mV
Input Bias Current	I_B	$V_{CM} = 0\text{ V}$, $T_A = 25^\circ\text{C}$		40	75	pA
Input Offset Current	I_{OS}	$V_{CM} = 0\text{ V}$, $T_A = 25^\circ\text{C}$		10	25	pA
Input Voltage Range ¹	IVR			12.5		V
			± 11			V
				–12.0		V
						V
Common-Mode Rejection	CMR	$V_{CM} = \pm 11\text{ V}$	76	90		dB
Power Supply Rejection Ratio	PSRR	$V_S = \pm 4.5\text{ V}$ to $\pm 18\text{ V}$		12	50	$\mu\text{V/V}$
Large Signal Voltage Gain	A_{VO}	$V_O = \pm 10\text{ V}$; $R_L = 2\text{ k}\Omega$	500	1100		V/mV
Output Voltage Swing	V_O	$R_L = 2\text{ k}\Omega$		12.5		V
			± 12.0			V
				–12.5		V
						V
Short-Circuit Current Limit	I_{SC}	Output shorted to ground		36		mA
			± 20		± 50	mA
				–33		mA
Supply Current	I_{SY}	No load; $V_O = 0\text{ V}$		5.6	7.0	mA
Slew Rate	SR	$R_L = 2\text{ k}\Omega$, $C_L = 50\text{ pF}$	18	22		V/ μs
Gain Bandwidth Product ²	GBW			4.7		MHz
Settling Time	t_S	10 V step 0.01%		0.9	1.2	μs
Phase Margin	θ_M	0 dB gain		55		Degree
Differential Input Impedance	Z_{IN}			$10^{12} \parallel 6$		$\Omega \parallel \text{pF}$
Open-Loop Output Resistance	R_O			35		Ω
Voltage Noise	e_n p-p	0.1 Hz to 10 Hz		2		$\mu\text{V p-p}$
Voltage Noise Density	e_n	$f_o = 10\text{ Hz}$		75		$\text{nV}/\sqrt{\text{Hz}}$
		$f_o = 100\text{ Hz}$		26		$\text{nV}/\sqrt{\text{Hz}}$
		$f_o = 1\text{ kHz}$		17		$\text{nV}/\sqrt{\text{Hz}}$
		$f_o = 10\text{ kHz}$		16		$\text{nV}/\sqrt{\text{Hz}}$
		$f_o = 1\text{ kHz}$		0.003		$\text{pA}/\sqrt{\text{Hz}}$
Current Noise Density	i_n	$f_o = 1\text{ kHz}$				$\text{pA}/\sqrt{\text{Hz}}$
Voltage Supply Range	V_S		± 4.5	± 15	± 18	V

¹ Guaranteed by CMR test.

² Guaranteed by design.

$V_S = \pm 15\text{ V}$, $-55^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$ for A grade, unless otherwise noted.

Table 3.

Parameter	Symbol	Conditions	OP249A			Unit
			Min	Typ	Max	
Offset Voltage	V_{OS}	$V_{CM} = 0\text{ V}$		0.12	1.0	mV
Offset Voltage Temperature Coefficient	TCV_{OS}	$V_{CM} = 0\text{ V}$		1	10	$\mu\text{V}/^\circ\text{C}$
Input Bias Current ¹	I_B			4	20	nA
Input Offset Current ¹	I_{OS}			0.04	4	nA
Input Voltage Range ²	IVR			12.5		V
			± 11			V
				-12.5		V
						V
Common-Mode Rejection	CMR	$V_{CM} = \pm 11\text{ V}$	76	110		dB
Power Supply Rejection Ratio	PSRR	$V_S = \pm 4.5\text{ V}$ to $\pm 18\text{ V}$		5	50	$\mu\text{V}/\text{V}$
Large Signal Voltage Gain	A_{VO}	$R_L = 2\text{ k}\Omega$; $V_O = \pm 10\text{ V}$	500	1400		V/mV
Output Voltage Swing	V_O	$R_L = 2\text{ k}\Omega$		12.5		V
			± 12			V
				-12.5		V
Supply Current	I_{SY}	No load, $V_O = 0\text{ V}$		5.6	7.0	mA

¹ $T_A = 125^\circ\text{C}$.

² Guaranteed by CMR test.

$V_S = \pm 15\text{ V}$, $-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$, unless otherwise noted.

Table 4.

Parameter	Symbol	Conditions	OP249F			OP249G			Unit
			Min	Typ	Max	Min	Typ	Max	
Offset Voltage	V_{OS}	$V_{CM} = 0\text{ V}$		0.5	1.1		1.0	3.6	mV
Offset Voltage Temperature Coefficient	TCV_{OS}	$V_{CM} = 0\text{ V}$		2.2	12		6	25	$\mu\text{V}/^\circ\text{C}$
Input Bias Current ¹	I_B			0.3	4.0		0.5	4.5	nA
Input Offset Current ¹	I_{OS}			0.02	1.2		0.04	1.5	nA
Input Voltage Range ²	IVR			12.5			12.5		V
			± 11			± 11			V
				-12.5			-12.5		V
									V
Common-Mode Rejection	CMR	$V_{CM} = \pm 11\text{ V}$	80	90		76	95		dB
Power Supply Rejection Ratio	PSRR	$V_S = \pm 4.5\text{ V}$ to $\pm 18\text{ V}$		7	100		10	100	$\mu\text{V}/\text{V}$
Large Signal Voltage Gain	A_{VO}	$R_L = 2\text{ k}\Omega$; $V_O = \pm 10\text{ V}$	250	1200		250	1200		V/mV
Output Voltage Swing	V_O	$R_L = 2\text{ k}\Omega$		12.5			12.5		V
			± 12			± 12.0			V
				-12.5			-12.5		V
Supply Current	I_{SY}	No load, $V_O = 0\text{ V}$		5.6	7.0		5.6	7.0	mA

¹ $T_A = 85^\circ\text{C}$.

² Guaranteed by CMR test.

ABSOLUTE MAXIMUM RATINGS

Table 5.

Parameter ¹	Rating
Supply Voltage	±18 V
Input Voltage ²	±18 V
Differential Input Voltage ²	36 V
Output Short-Circuit Duration	Indefinite
Storage Temperature Range	–65°C to +175°C
Operating Temperature Range	
OP249A (Q)	–55°C to +125°C
OP249F (Q)	–40°C to +85°C
OP249G (N, R)	–40°C to +85°C
Junction Temperature Range	
OP249A (Q), OP249F (Q)	–65°C to +175°C
OP249G (N, R)	–65°C to +150°C
Lead Temperature (Soldering, 60 sec)	300°C

¹ Absolute maximum ratings apply to packaged parts, unless otherwise noted.

² For supply voltages less than ±18 V, the absolute maximum input voltage is equal to the supply voltage.

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Table 6. Thermal Resistance

Package Type	θ_{JA} ¹	θ_{JC}	Unit
8-Lead CERDIP (Q)	134	12	°C/W
8-Lead PDIP (N)	96	37	°C/W
8-Lead SOIC (R)	150	41	°C/W

¹ θ_{JA} is specified for worst-case mounting conditions, that is, θ_{JA} is specified for device in socket for CERDIP and PDIP packages; θ_{JA} is specified for device soldered to printed circuit board for SOIC package.

ESD CAUTION



ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

TYPICAL PERFORMANCE CHARACTERISTICS

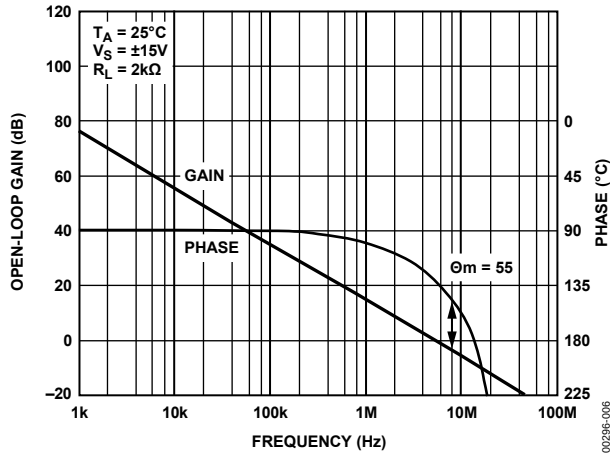


Figure 6. Open-Loop Gain, Phase vs. Frequency

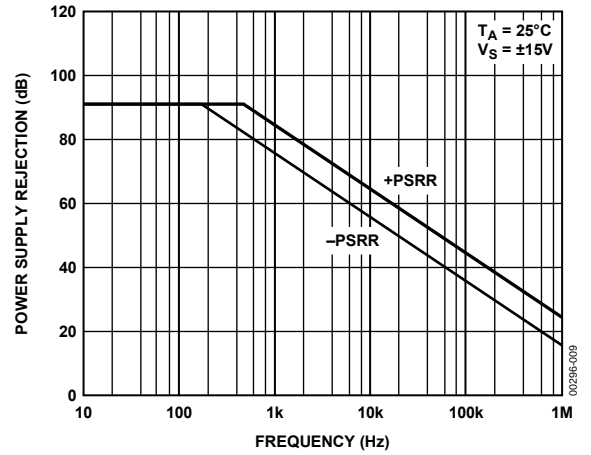


Figure 9. Power Supply Rejection vs. Frequency

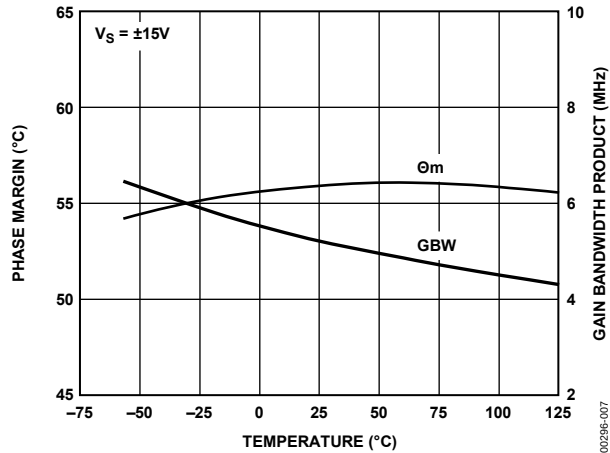


Figure 7. Phase Margin, Gain Bandwidth Product vs. Temperature

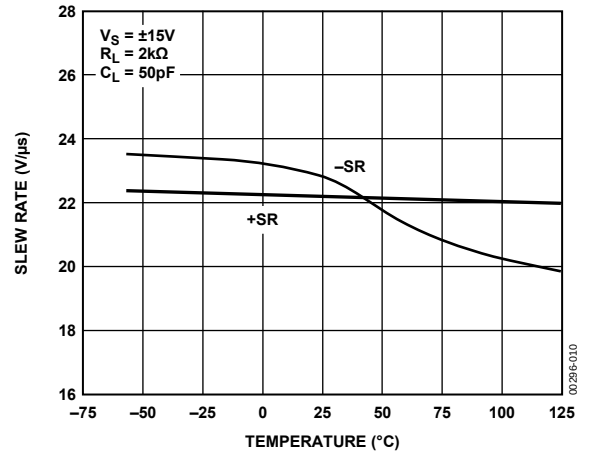


Figure 10. Slew Rate vs. Temperature

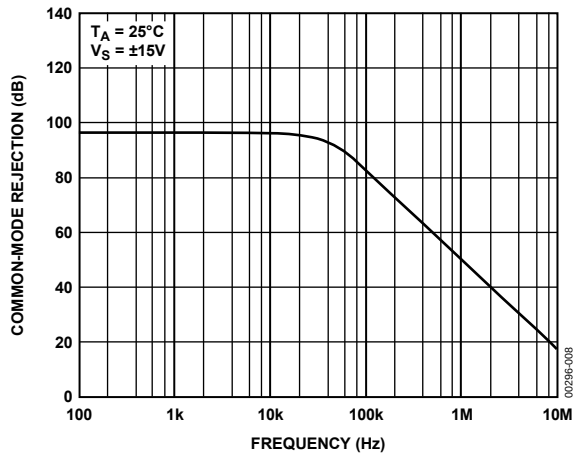


Figure 8. Common-Mode Rejection vs. Frequency

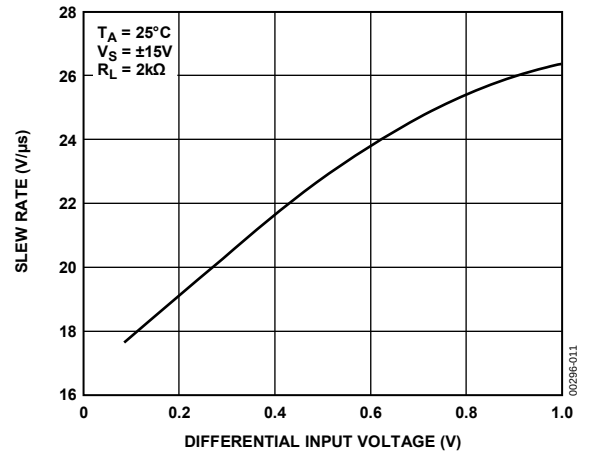


Figure 11. Slew Rate vs. Differential Input Voltage

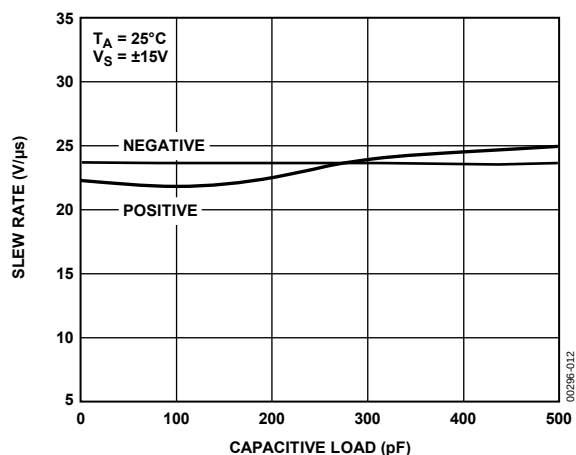


Figure 12. Slew Rate vs. Capacitive Load

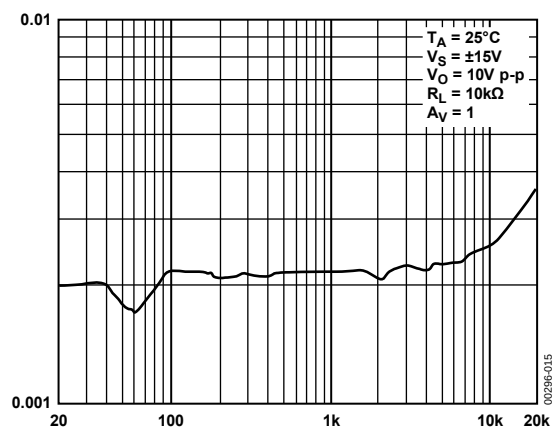


Figure 15. Distortion vs. Frequency

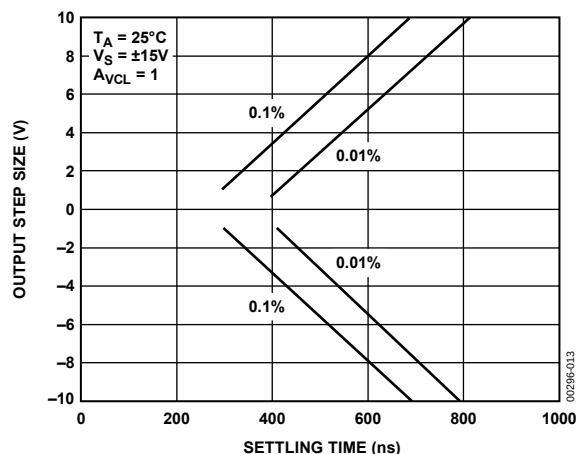


Figure 13. Step Size vs. Settling Time

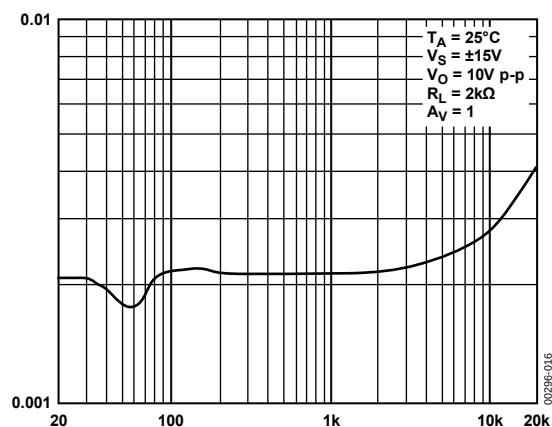


Figure 16. Distortion vs. Frequency

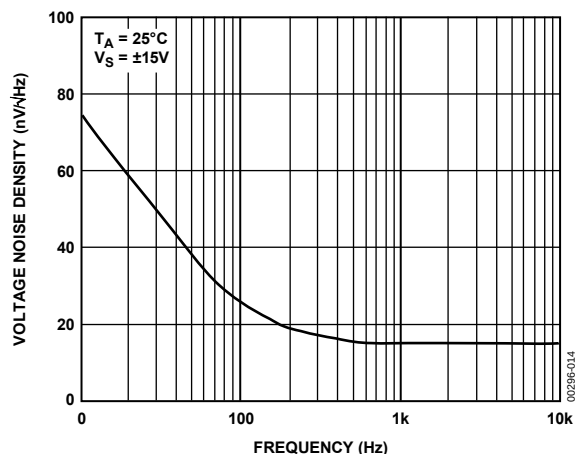


Figure 14. Voltage Noise Density vs. Frequency

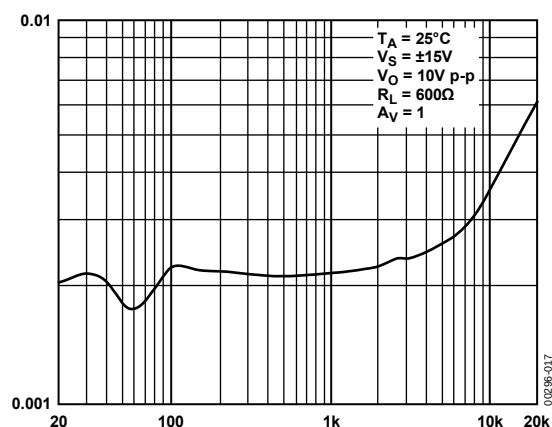


Figure 17. Distortion vs. Frequency

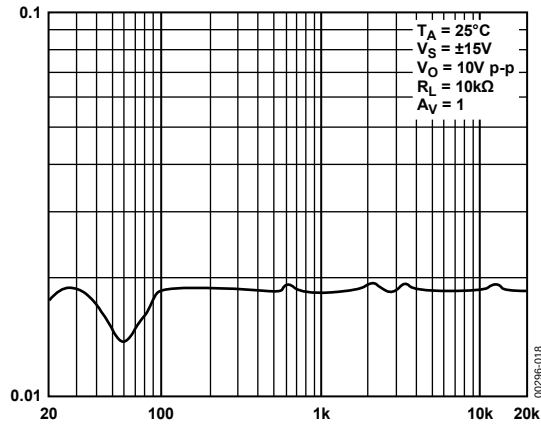


Figure 18. Distortion vs. Frequency

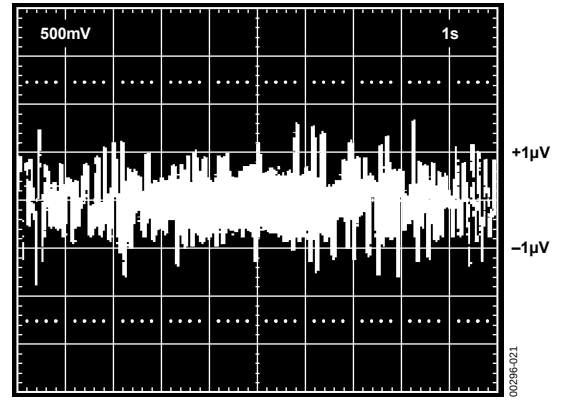


Figure 21. Low Frequency Noise

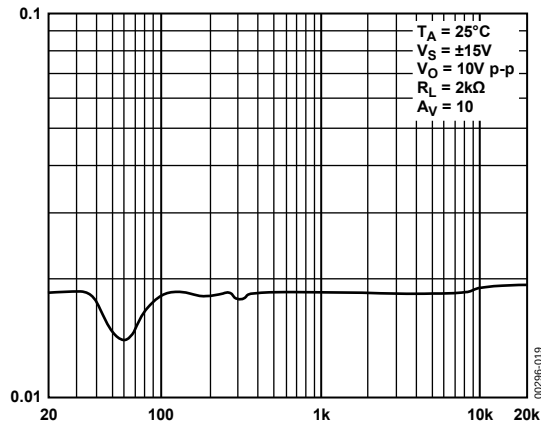


Figure 19. Distortion vs. Frequency

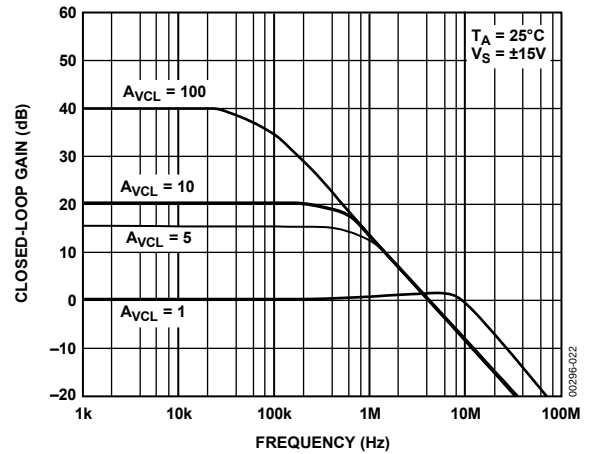


Figure 22. Closed-Loop Gain vs. Frequency

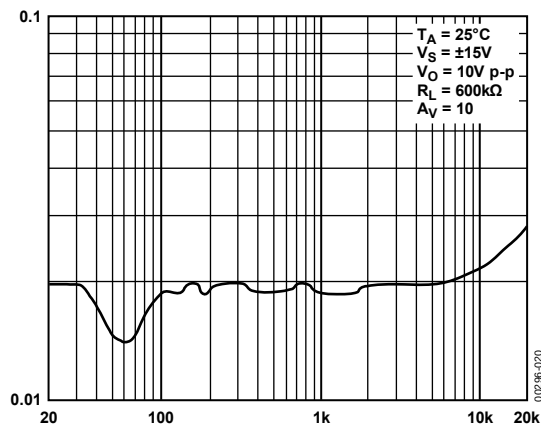


Figure 20. Distortion vs. Frequency

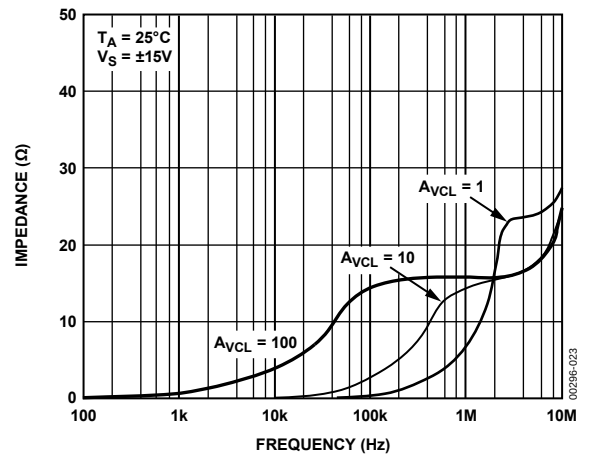


Figure 23. Closed-Loop Output Impedance vs. Frequency

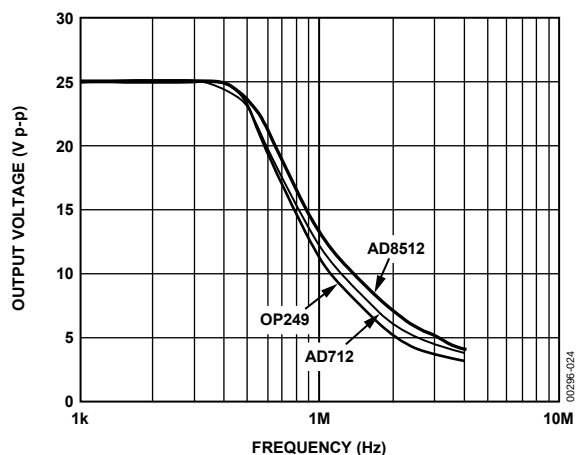


Figure 24. Output Voltage vs. Frequency

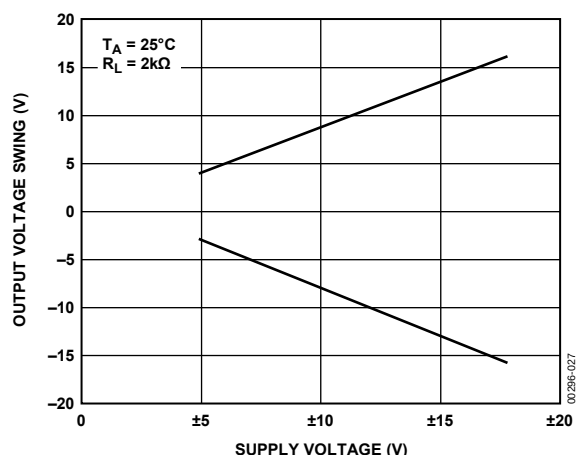


Figure 27. Output Voltage Swing vs. Supply Voltage

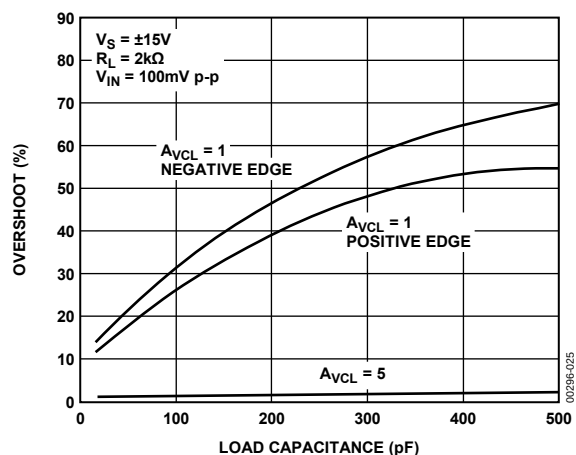


Figure 25. Small Overshoot vs. Load Capacitance

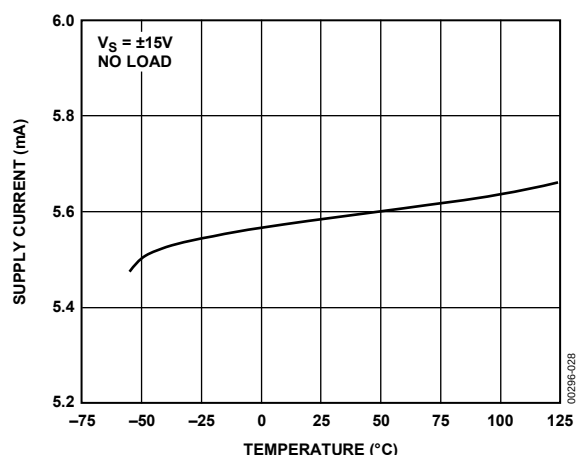


Figure 28. Supply Current vs. Temperature

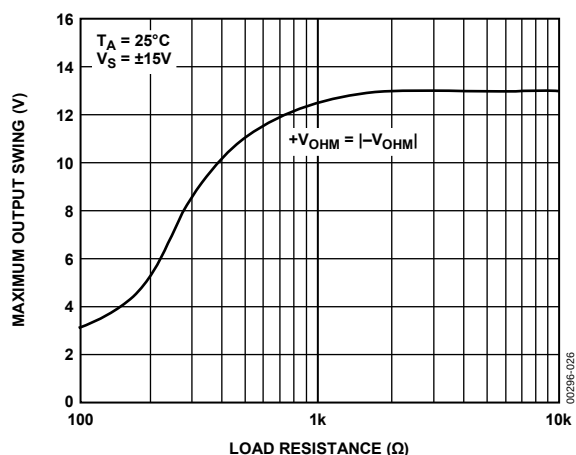


Figure 26. Maximum Output Voltage Swing vs. Load Resistance

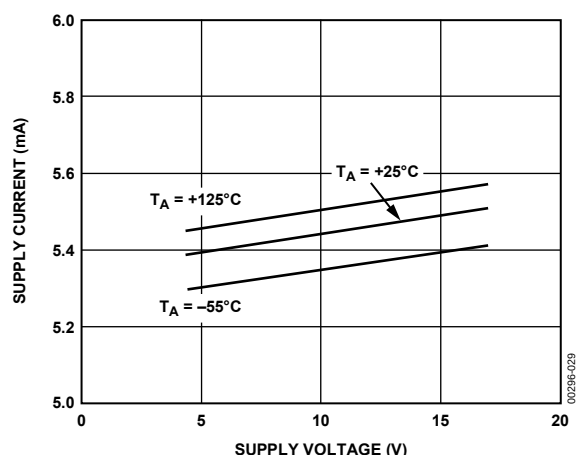


Figure 29. Supply Current vs. Supply Voltage

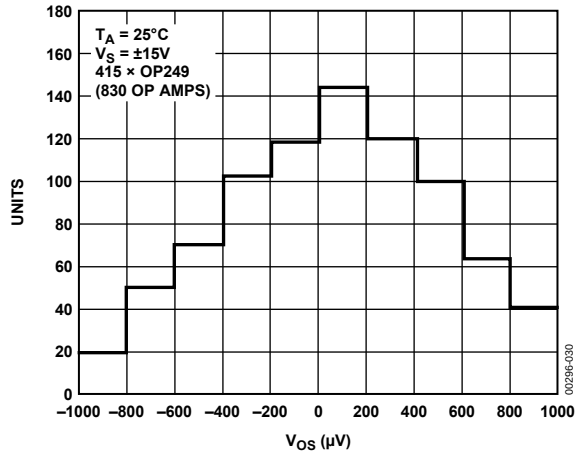


Figure 30. V_{OS} Distribution (N-8)

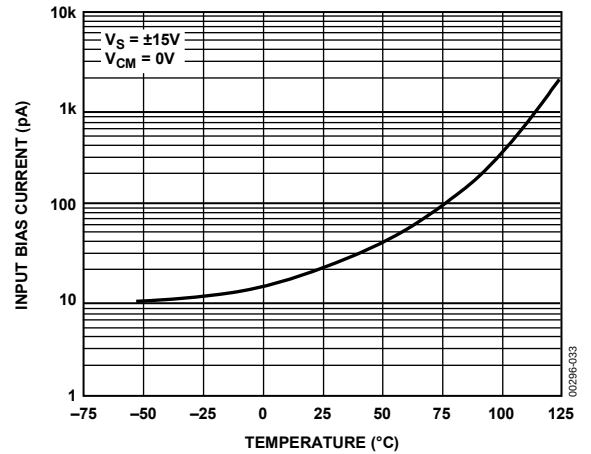


Figure 33. Input Bias Current vs. Temperature

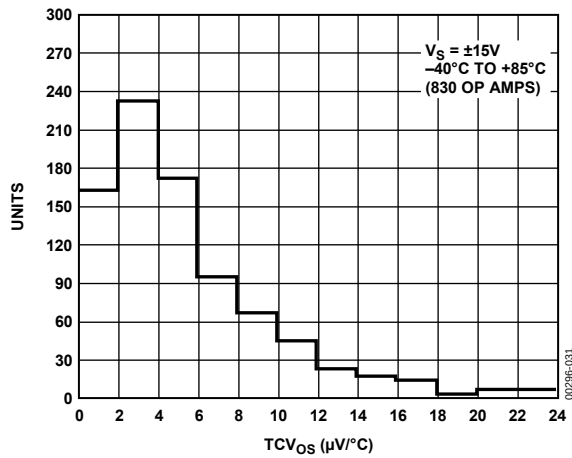


Figure 31. TCV_{OS} Distribution (N-8)

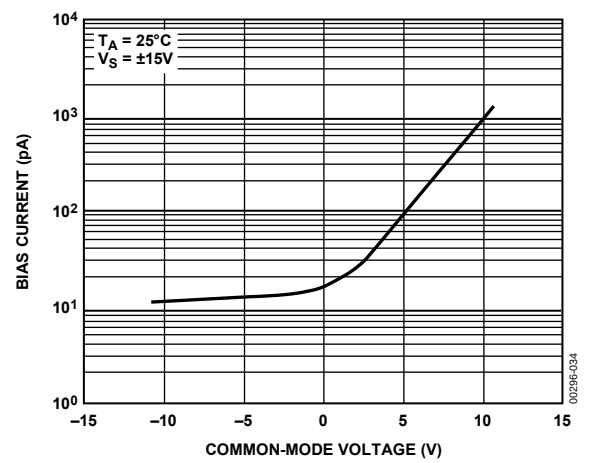


Figure 34. Bias Current vs. Common-Mode Voltage

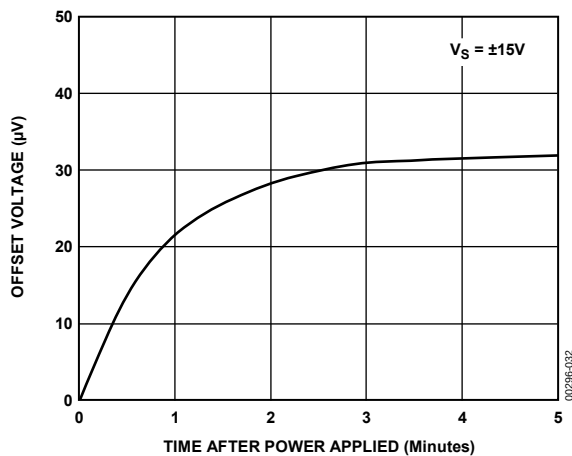


Figure 32. Offset Voltage Warm-Up Drift

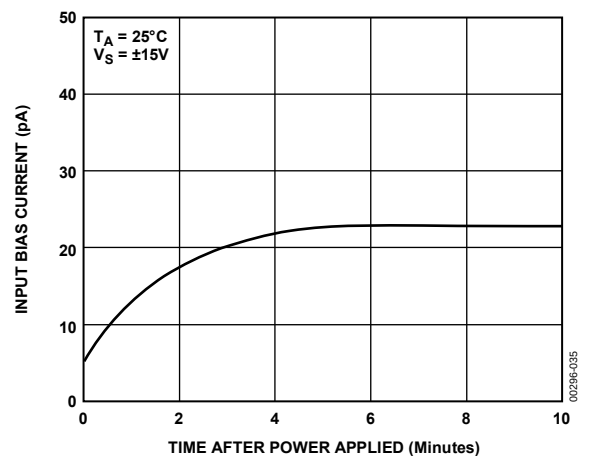


Figure 35. Bias Current Warm-Up Drift

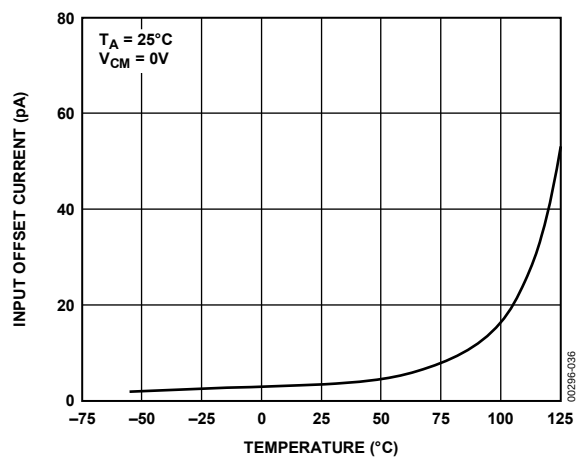


Figure 36. Input Offset Current vs. Temperature

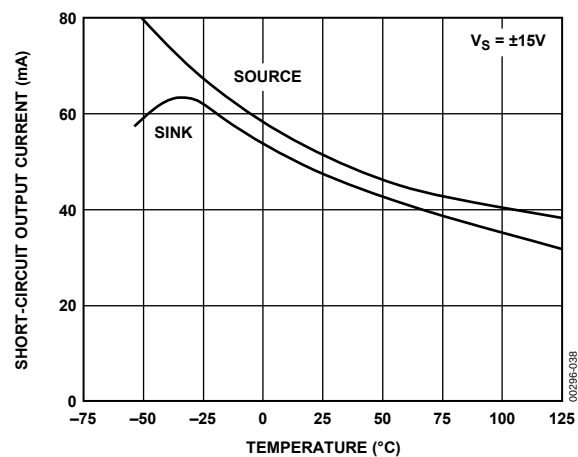


Figure 38. Short-Circuit Output Current vs. Junction Temperature

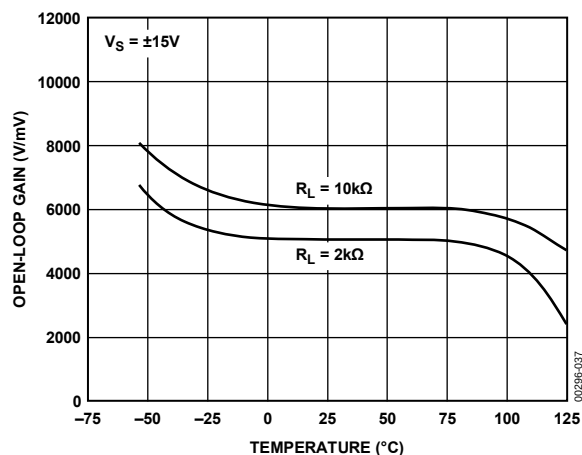


Figure 37. Open-Loop Gain vs. Temperature

APPLICATIONS INFORMATION

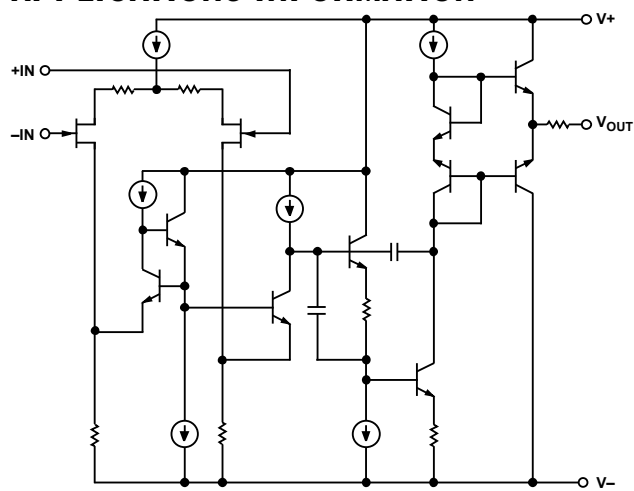


Figure 39. Simplified Schematic (1/2 OP249)

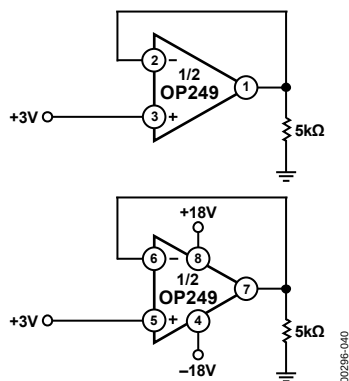
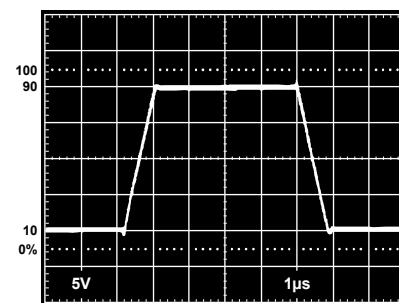


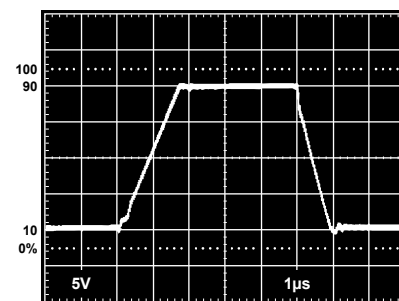
Figure 40. Burn-In Circuit

The OP249 represents a reliable JFET amplifier design, featuring an excellent combination of dc precision and high speed. A rugged output stage provides the ability to drive a $600\ \Omega$ load and still maintain a clean ac response. The OP249 features a large signal response that is more linear and symmetric than previously available JFET input amplifiers. Figure 41 compares the large signal response of the OP249 to other industry-standard dual JFET amplifiers.

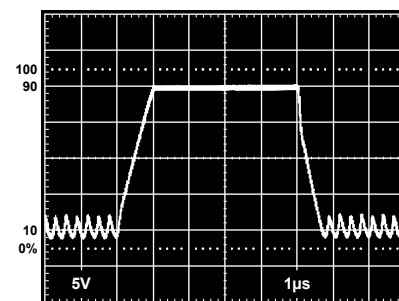
Typically, the slewing performance of the JFET amplifier is specified as a number of $V/\mu s$. There is no discussion on the quality, that is, linearity and symmetry of the slewing response.



A) OP249



B) LT1057



C) AD712

Figure 41. Large-Signal Transient Response, $A_V = 1$, $V_{IN} = 20\ V_{p-p}$, $Z_L = 2\ k\Omega/200\ pF$, $V_S = \pm 15\ V$

The OP249 was carefully designed to provide symmetrically matched slew characteristics in both the negative and positive directions, even when driving a large output load.

The slewing limitation of the amplifier determines the maximum frequency at which a sinusoidal output can be obtained without significant distortion. However, it is important to note that the nonsymmetric slewing typical of previously available JFET amplifiers adds a higher series of harmonic energy content to the resulting response—and an additional dc output component. Examples of potential problems of nonsymmetric slewing behavior can be in audio amplifier applications, where a natural low distortion sound quality is desired and in servo or signal processing systems where a net dc offset cannot be tolerated. The linear and symmetric slewing feature of the OP249 makes it an ideal choice for applications that exceed the full power bandwidth range of the amplifier.

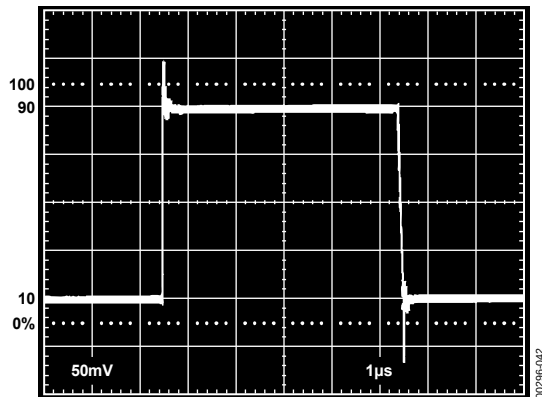


Figure 42. Small-Signal Transient Response,
 $A_v = 1$, $Z_L = 2 \text{ k}\Omega \parallel 100 \text{ pF}$, No Compensation, $V_S = \pm 15 \text{ V}$

As with most JFET input amplifiers, the output of the OP249 can undergo phase inversion if either input exceeds the specified input voltage range. Phase inversion does not damage the amplifier, nor does it cause an internal latch-up condition.

Supply decoupling should be used to overcome inductance and resistance associated with supply lines to the amplifier. A $0.1 \mu\text{F}$ and a $10 \mu\text{F}$ capacitor should be placed between each supply pin and ground.

OPEN-LOOP GAIN LINEARITY

The OP249 has both an extremely high open-loop gain of 1 kV/mV minimum and constant gain linearity, which enhances its dc precision and provides superb accuracy in high closed-loop gain applications. Figure 43 illustrates the typical open-loop gain linearity—high gain accuracy is assured, even when driving a 600Ω load.

OFFSET VOLTAGE ADJUSTMENT

The inherent low offset voltage of the OP249 makes offset adjustments unnecessary in most applications. However, where a lower offset error is required, balancing can be performed with simple external circuitry, as shown in Figure 44 and Figure 45.

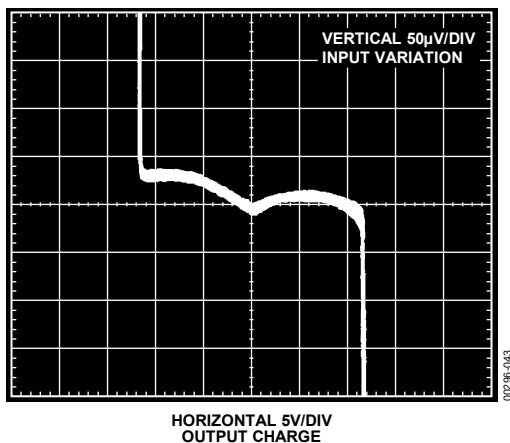


Figure 43. Open-Loop Gain Linearity; Variation in Open-Loop Gain Results in Errors in High Closed-Loop Gain Circuits; $R_L = 600 \Omega$, $V_S = \pm 15 \text{ V}$

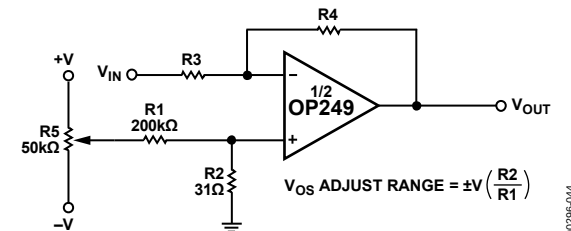


Figure 44. Offset Adjustment for Inverting Amplifier Configuration

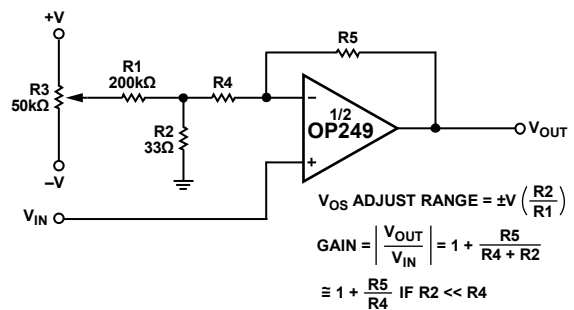


Figure 45. Offset Adjustment for Noninverting Amplifier Configuration

In Figure 44, the offset adjustment is made by supplying a small voltage at the noninverting input of the amplifier. Resistors $R1$ and $R2$ attenuate the potentiometer voltage, providing a $\pm 2.5 \text{ mV}$ (with $V_S = \pm 15 \text{ V}$) adjustment range, referred to the input. Figure 45 shows the offset adjustment for the noninverting amplifier configuration, also providing a $\pm 2.5 \text{ mV}$ adjustment range. As shown in the equations in Figure 45, if $R4$ is not much greater than $R2$, a resulting closed-loop gain error must be accounted for.

SETTLING TIME

The settling time is the time between when the input signal begins to change and when the output permanently enters a prescribed error band. The error bands on the output are 5 mV and 0.5 mV , respectively, for 0.1% and 0.01% accuracy.

Figure 46 shows the settling time of the OP249, which is typically 870 ns . Moreover, problems in settling response, such as thermal tails and long-term ringing, are nonexistent.

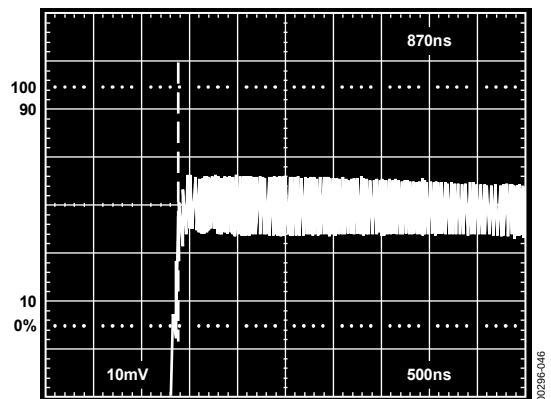


Figure 46. Settling Characteristics of the OP249 to 0.01%

DAC OUTPUT AMPLIFIER

Unity-gain stability, a low offset voltage of 300 μV typical, and a fast settling time of 870 ns to 0.01%, makes the OP249 an ideal amplifier for fast DACs.

For CMOS DAC applications, the low offset voltage of the OP249 results in excellent linearity performance. CMOS DACs, such as the PM7545, typically have a code-dependent output resistance variation between 11 $\text{k}\Omega$ and 33 $\text{k}\Omega$. The change in output resistance, in conjunction with the 11 $\text{k}\Omega$ feedback resistor, results in a noise gain change, which causes variations in the offset error, increasing linearity errors. The OP249 features low offset voltage error, minimizing this effect and maintaining 12-bit linearity performance over the full-scale range of the converter.

Because the DAC output capacitance appears at the inputs of the op amp, it is essential that the amplifier be adequately compensated. Compensation increases the phase margin and ensures an optimal overall settling response. The required lead compensation is achieved with Capacitor C in Figure 48.

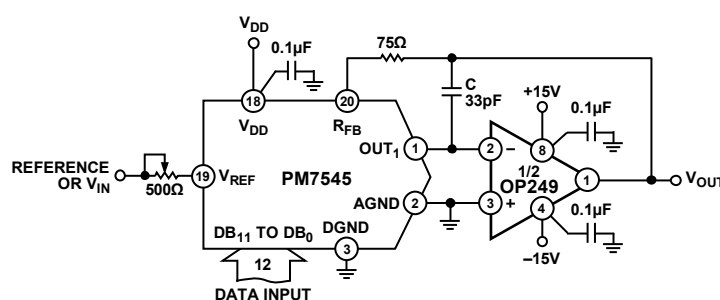


Figure 47. Fast Settling and Low Offset Error of the OP249 Enhances CMOS DAC Performance—Unipolar Operation

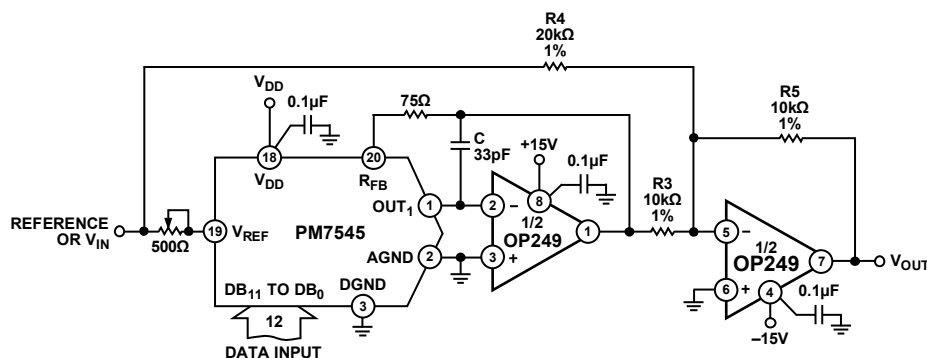
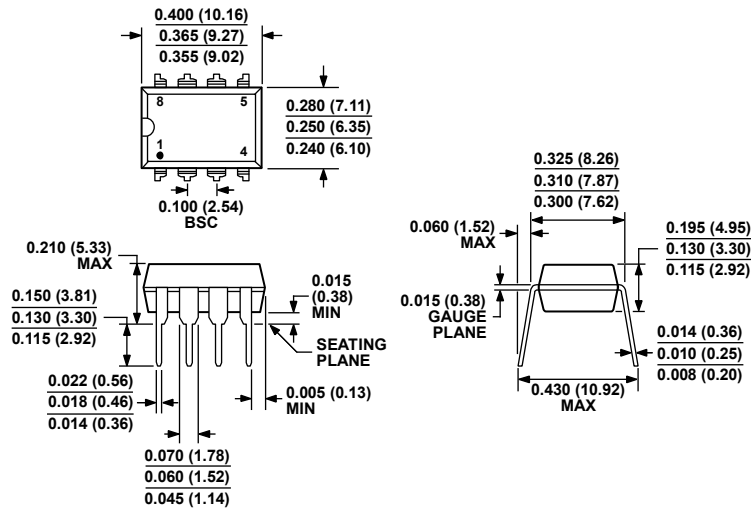


Figure 48. Fast Settling and Low Offset Error of the OP249 Enhances CMOS DAC Performance—Bipolar Operation

OUTLINE DIMENSIONS

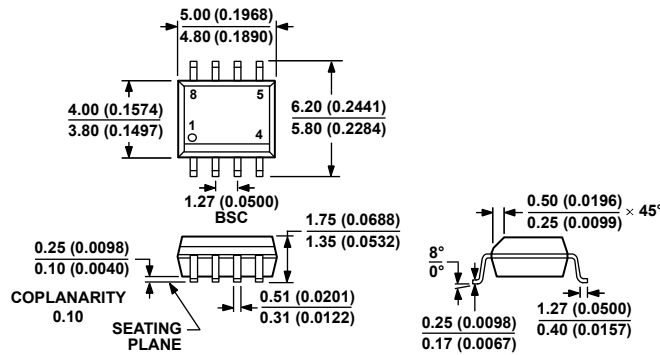


COMPLIANT TO JEDEC STANDARDS MS-001
CONTROLLING DIMENSIONS ARE IN INCHES; MILLIMETER DIMENSIONS (IN PARENTHESES) ARE ROUNDED-OFF INCH EQUIVALENTS FOR REFERENCE ONLY AND ARE NOT APPROPRIATE FOR USE IN DESIGN. CORNER LEADS MAY BE CONFIGURED AS WHOLE OR HALF LEADS.

Figure 52. 8-Lead Plastic Dual In-Line Package [PDIP]
Narrow Body
(N-8)

Dimensions shown in inches and (millimeters)

070606-A

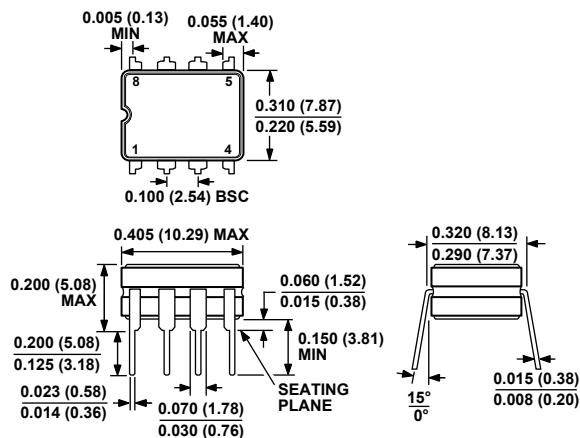


COMPLIANT TO JEDEC STANDARDS MS-012-AA
CONTROLLING DIMENSIONS ARE IN MILLIMETERS; INCH DIMENSIONS (IN PARENTHESES) ARE ROUNDED-OFF MILLIMETER EQUIVALENTS FOR REFERENCE ONLY AND ARE NOT APPROPRIATE FOR USE IN DESIGN.

Figure 53. 8-Lead Standard Small Outline Package [SOIC_N]
Narrow Body
(R-8)

Dimensions shown in millimeters and (inches)

012407-A



CONTROLLING DIMENSIONS ARE IN INCHES; MILLIMETER DIMENSIONS (IN PARENTHESES) ARE ROUNDED-OFF INCH EQUIVALENTS FOR REFERENCE ONLY AND ARE NOT APPROPRIATE FOR USE IN DESIGN.

Figure 54. 8-Lead Ceramic Dual In-Line Package [CERDIP] (Q-8)

Dimensions shown in inches and (millimeters)

ORDERING GUIDE

Model ¹	Temperature Range	Package Description	Package Option
OP249AZ	–55°C to +125°C	8-Lead CERDIP	Q-8
OP249FZ	–40°C to +85°C	8-Lead CERDIP	Q-8
OP249GP	–40°C to +85°C	8-Lead PDIP	N-8
OP249GPZ	–40°C to +85°C	8-Lead PDIP	N-8
OP249GS	–40°C to +85°C	8-Lead SOIC_N	R-8
OP249GS-REEL	–40°C to +85°C	8-Lead SOIC_N	R-8
OP249GS-REEL7	–40°C to +85°C	8-Lead SOIC_N	R-8
OP249GSZ	–40°C to +85°C	8-Lead SOIC_N	R-8
OP249GSZ-REEL	–40°C to +85°C	8-Lead SOIC_N	R-8
OP249GSZ-REEL7	–40°C to +85°C	8-Lead SOIC_N	R-8

¹ Z = RoHS Compliant Part.

For military processed devices, see the standard microcircuit drawings (SMD) available at www.dscc.dla.mil/programs/milspec/default.asp.

Table 7.

SMD Part Number	Analog Devices, Inc. Equivalent
5962-9151901M2A	OP249ARCMDA
5962-9151901MPA	OP249AZMDA

NOTES

OP249

NOTES

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

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